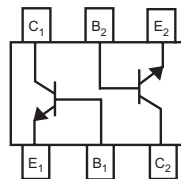
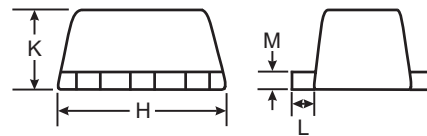
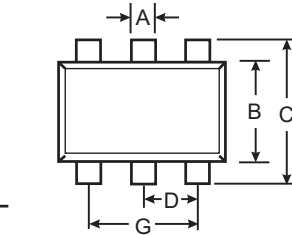


Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMDT2907V)
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT-563, Molded Plastic
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Polarity: See Diagrams Below
- Marking & Type Code Information: See Last Page
- Ordering Information: See Last Page
- Weight: 0.003 grams (approx.)



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.25
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.56	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	—
All Dimensions in mm			

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous	I _C	600	mA
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

Thermal Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 3)	P _d	150	mW
Thermal Resistance, Junction to Ambient (Note 3)	R _{θJA}	833	°C/W

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	75	—	V	$I_C = 10\mu\text{A}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	$I_C = 10\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	$I_E = 10\mu\text{A}$, $I_C = 0$
Collector Cutoff Current	I_{CBO}	—	10	nA μA	$V_{CB} = 60\text{V}$, $I_E = 0$ $V_{CB} = 60\text{V}$, $I_E = 0$, $T_A = 150^\circ\text{C}$
Collector Cutoff Current	I_{CEX}	—	10	nA	$V_{CE} = 60\text{V}$, $V_{EB(OFF)} = 3.0\text{V}$
Emitter Cutoff Current	I_{EBO}	—	10	nA	$V_{EB} = 3.0\text{V}$, $I_C = 0$
Base Cutoff Current	I_{BL}	—	20	nA	$V_{CE} = 60\text{V}$, $V_{EB(OFF)} = 3.0\text{V}$
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h_{FE}	35 50 75 100 40 50 35	— — — 300 — — —	—	$I_C = 100\mu\text{A}$, $V_{CE} = 10\text{V}$ $I_C = 1.0\text{mA}$, $V_{CE} = 10\text{V}$ $I_C = 10\text{mA}$, $V_{CE} = 10\text{V}$ $I_C = 150\text{mA}$, $V_{CE} = 10\text{V}$ $I_C = 500\text{mA}$, $V_{CE} = 10\text{V}$ $I_C = 10\text{mA}$, $V_{CE} = 10\text{V}$, $T_A = -55^\circ\text{C}$ $I_C = 150\text{mA}$, $V_{CE} = 1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.3 1.0	V	$I_C = 150\text{mA}$, $I_B = 15\text{mA}$ $I_C = 500\text{mA}$, $I_B = 50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.6 —	1.2 2.0	V	$I_C = 150\text{mA}$, $I_B = 15\text{mA}$ $I_C = 500\text{mA}$, $I_B = 50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	8	pF	$V_{CB} = 10\text{V}$, $f = 1.0\text{MHz}$, $I_E = 0$
Input Capacitance	C_{ibo}	—	25	pF	$V_{EB} = 0.5\text{V}$, $f = 1.0\text{MHz}$, $I_C = 0$
Current Gain-Bandwidth Product	f_T	300	—	MHz	$V_{CE} = 20\text{V}$, $I_C = 20\text{mA}$, $f = 100\text{MHz}$
Noise Figure	NF	—	4.0	dB	$V_{CE} = 10\text{V}$, $I_C = 100\mu\text{A}$, $R_S = 1.0\text{k}\Omega$, $f = 1.0\text{kHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	10	ns	$V_{CC} = 30\text{V}$, $I_C = 150\text{mA}$, $V_{BE(off)} = -0.5\text{V}$, $I_{B1} = 15\text{mA}$
Rise Time	t_r	—	25	ns	
Storage Time	t_s	—	225	ns	$V_{CC} = 30\text{V}$, $I_C = 150\text{mA}$, $I_{B1} = I_{B2} = 15\text{mA}$
Fall Time	t_f	—	60	ns	

Notes: 4. Short duration test pulse used to minimize self-heating effect.

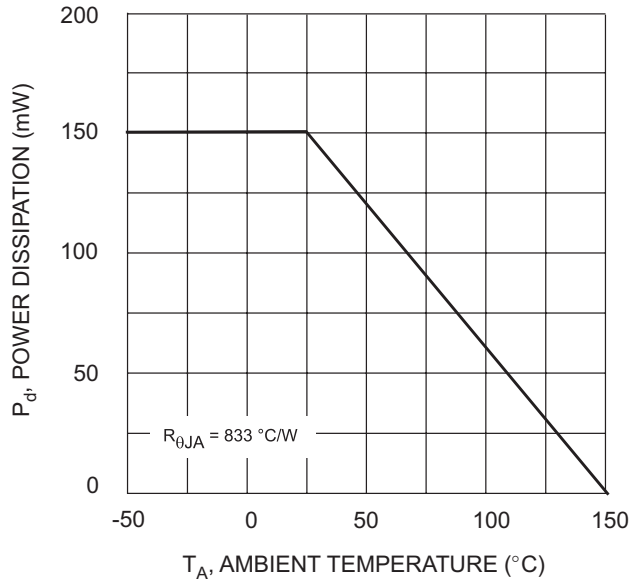


Fig. 1, Derating Curve - Total

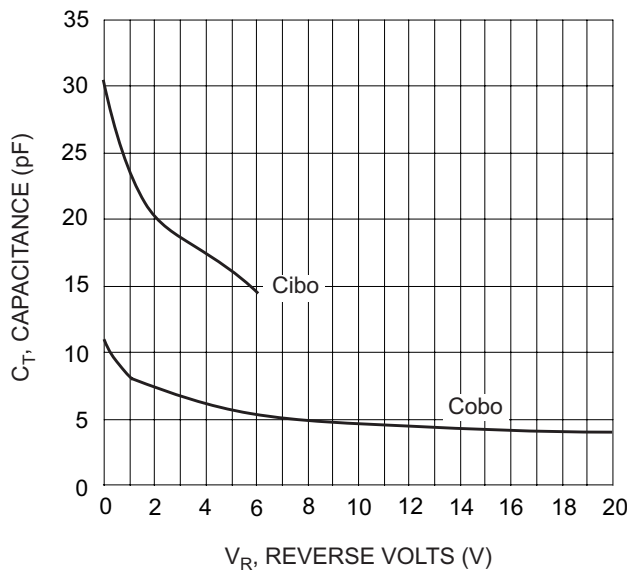


Fig. 3 Typical Capacitance Characteristics

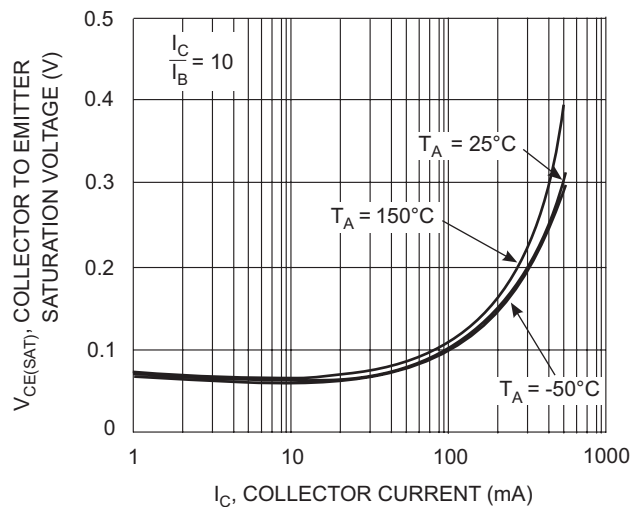


Fig. 5 Collector Emitter Saturation Voltage vs. Collector Current

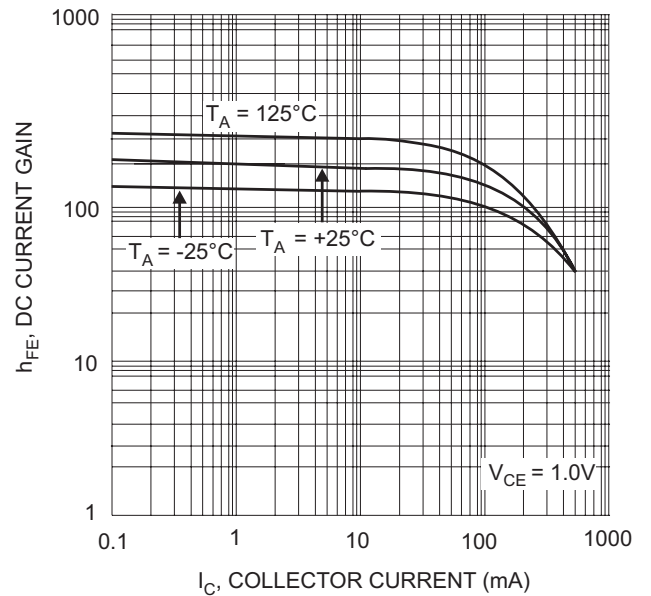


Fig. 2 Typical DC Current Gain vs Collector Current

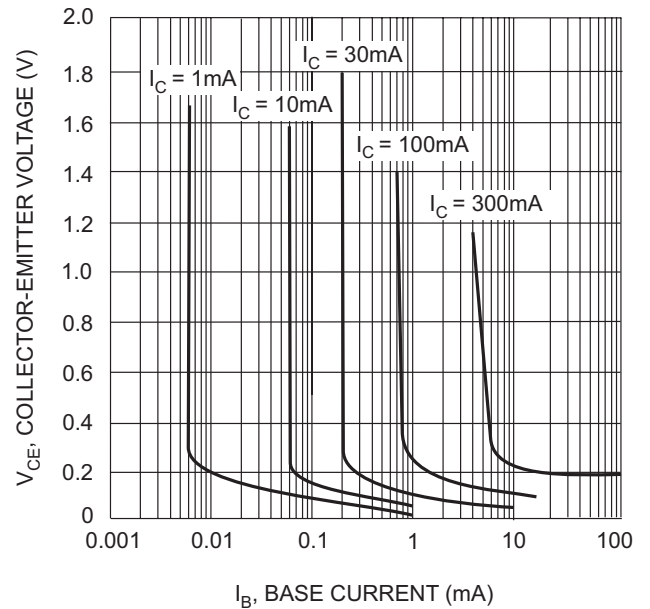


Fig. 4 Typical Collector Saturation Region

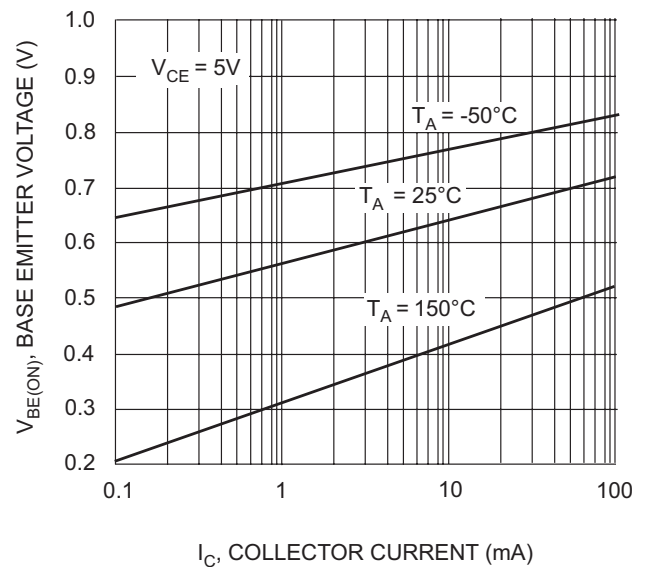


Fig. 6 Base Emitter Voltage vs. Collector Current

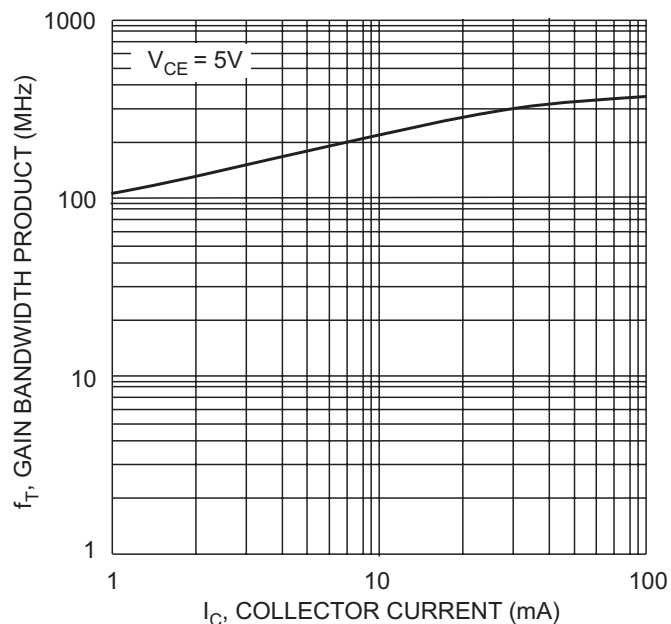


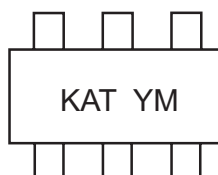
Fig. 7 Gain Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
MMDT2222V-7	SOT-563	3000/Tape & Reel

Notes: 5. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



KAT = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: R = 2004
 M = Month ex: 9 = September

Date Code Key

Year							2004	2005	2006	2007	2008	2009
Code							R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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